Toshiba Schottky Barrier Rectifier Schottky Barrier Type

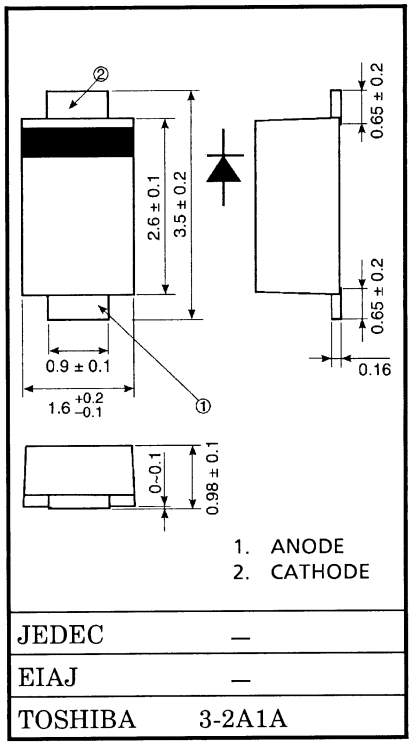
C R S 0 9

Switching Type Power Supply Applications

Portable Equipment Battery Applications

- Forward voltage: V_{FM} = 0.46 V (max)
- Average forward current: $I_{F\ (AV)}$ = 1.5 A
- Repetitive peak reverse voltage: V_{RRM} = 30 V
- Small package: "S-FLAT™" (Toshiba designation)

Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	3-2A1A

Weight : 0.013g

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F\ (AV)}$	1.5	A
Peak one cycle surge forward current (non-repetitive)	I_{FSM}	30 (50 Hz)	A
Junction temperature	T_j	−40~150	°C
Storage temperature	T_{stg}	−40~150	°C

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Peak forward voltage	$V_{FM\ (1)}$	I_{FM} = 0.1 A	—	0.35	—	V
	$V_{FM\ (2)}$	I_{FM} = 1.0 A	—	0.415	—	
	$V_{FM\ (3)}$	I_{FM} = 1.5 A	—	0.43	0.46	
Repetitive peak reverse current	$I_{RRM\ (1)}$	V_{RRM} = 5 V	—	0.8	—	μA
	$I_{RRM\ (2)}$	V_{RRM} = 30 V	—	10	50	
Junction capacitance	C_j	V_R = 10 V, f = 1.0 MHz	—	90	—	pF
Thermal resistance	$R_{th\ (j-a)}$	On ceramic substrate (soldering land 2 mm × 2 mm)	—	—	70	°C/W
		On glass-epoxy substrate (soldering land 6 mm × 6 mm)	—	—	140	

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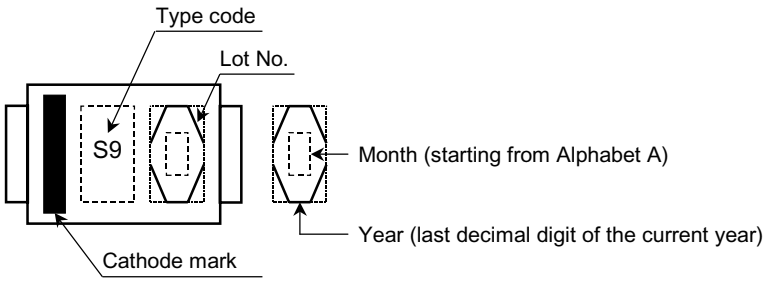
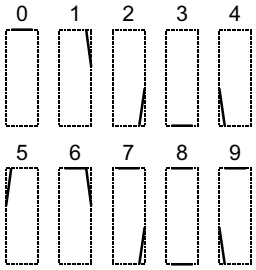
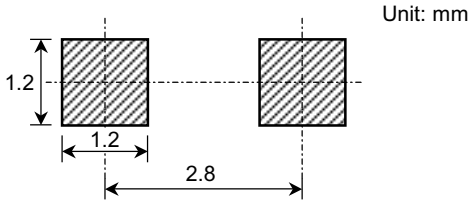
Marking



Following Indicates the Date of Manufacture



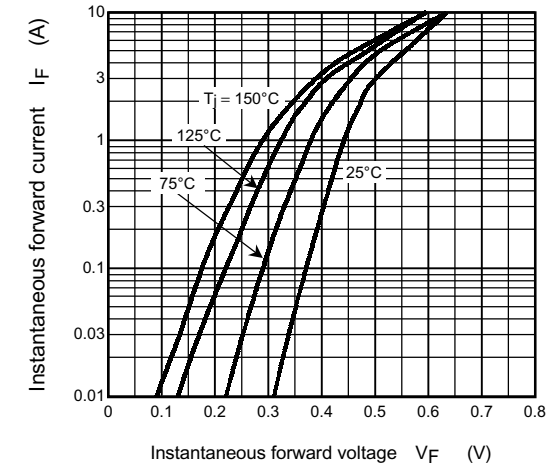
Standard Soldering Pad



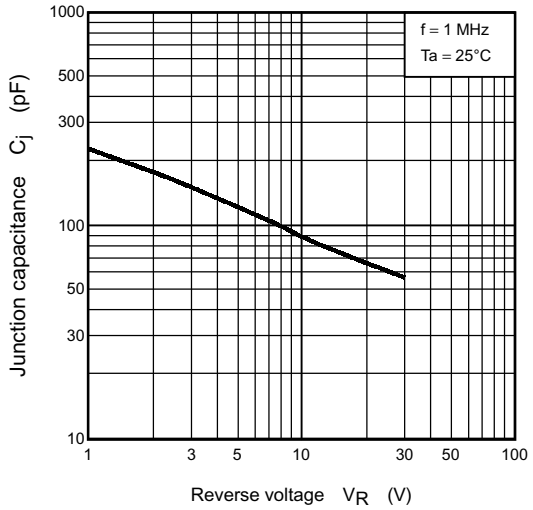
Handling Precaution

Schottky barrier diodes are having large-reverse-current-leakage characteristic compare to the other rectifier products. This current leakage and not proper operating temperature or voltage may cause thermal run.
Please take forward and reverse loss into consideration when you design.

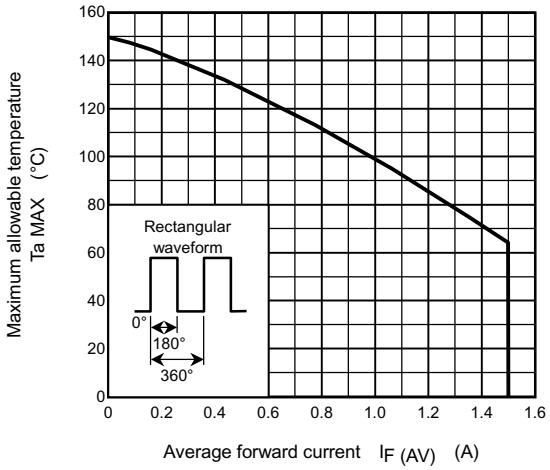
$I_F - V_F$



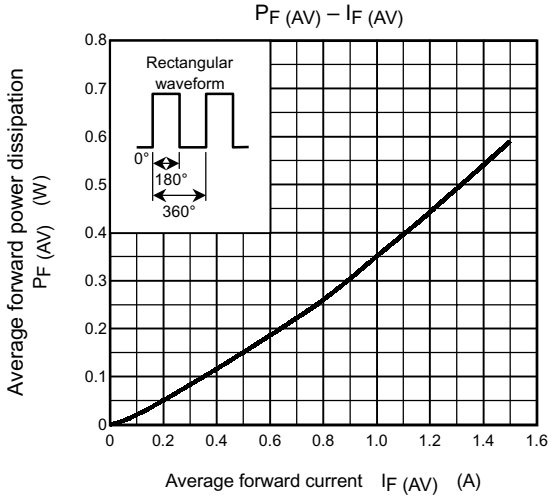
$C_j - V_R$ (typ.)



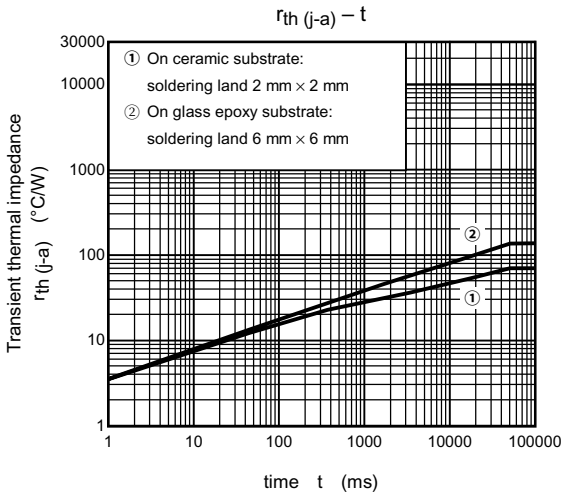
Ta MAX – $I_{F\ (AV)}$



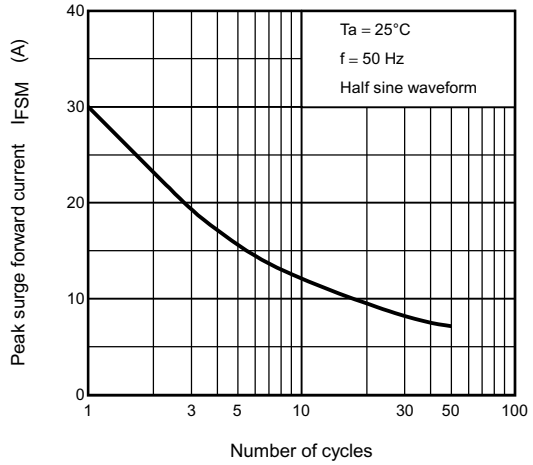
$P_{F\ (AV)} - I_{F\ (AV)}$



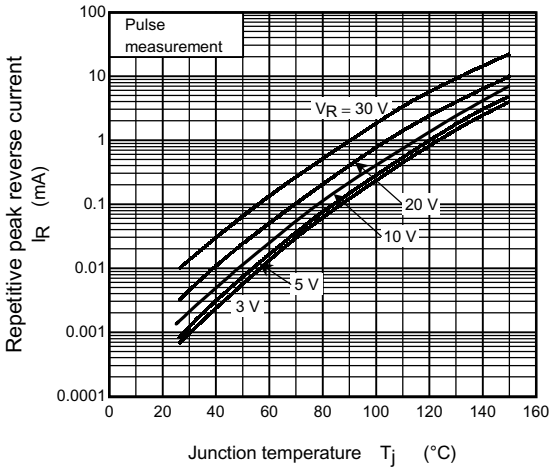
$r_{th\ (j\text{-}a)} - t$



Surge forward current (non-repetitive)



$I_R - T_j$ (typ.)



$P_{R\ (AV)} - V_R$ (typ.)